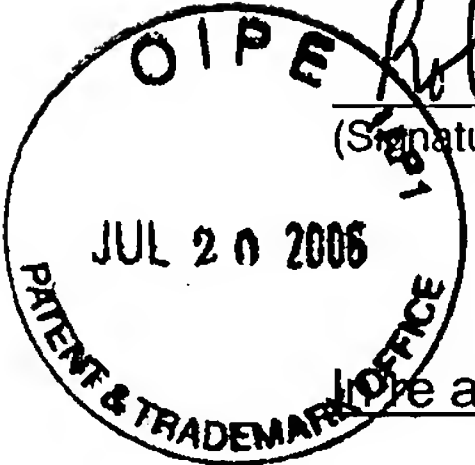


IFW

I hereby certify that this correspondence is being deposited in a first class mail envelope with the United States Postal Service addressed to : Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313. The applicant and/or attorney requests the date of deposit as the filing date.

Date of Deposit: ~~July 14, 2006~~ JULY 18, 2006 RCF
Depositor: Robert Faber

 Robert Faber ~~7/14/06~~ 7/18/06 RCF
(Signature & date)

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Pro application of _____:

Date: July 17, 2006 RCF

Huilong Zhu _____:

Group Art Unit: 2826

Serial No: 10/710,244 _____:

Examiner: Fazli Erdem

Filed: 06/29/2004 _____:

International Business Machines Corporation
2070 Route 52
Hopewell Junction, NY 12533

TITLE: STRUCTURES AND METHODS FOR MANUFACTURING P-TYPE MOSFET WITH GRADED EMBEDDED SILICON-GERMANIUM SOURCE-DRAIN AND/OR EXTENSION

INFORMATION DISCLOSURE STATEMENT

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Sir:

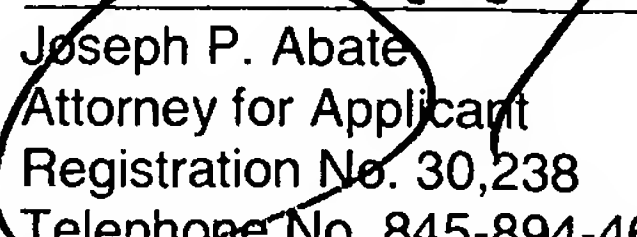
Pursuant to the duty of disclosure set forth in 37 C.F.R. 1.56, and further pursuant to the provisions of 37 C.F.R. 1.97 and 1.98, applicants hereby respectfully submit copies of the US and non-US patents and publications as listed on Form PTO-1449, attached hereto.

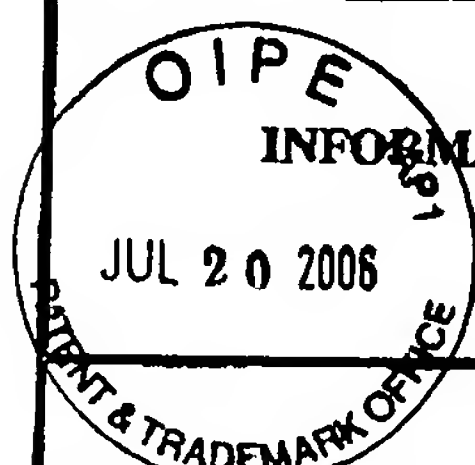
In citing these documents, no representation is made nor intended as to the pertinency or non-pertinency of the art, that better art than that listed is not available, or that other art is not applicable.

The Commissioner is hereby authorized to charge any and all fees for this submission to Deposit Account No. 09-0458.

Respectfully submitted,
Huilong Zhu

By

 19 July 2006
Joseph P. Abate
Attorney for Applicant
Registration No. 30,238
Telephone No. 845-894-4633
Fax No. 845-892-6363



Docket Number (Optional)		Application Number
EIS920040116US1		10/710,244
Applicant(s)		
Huiling Zhu		
Filing Date		Group Art Unit
06/29/2004		2811

U.S. PATENT DOCUMENTS

*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
		3,602,841	8-31-71	McGroddy			
		4,665,415	5-12-87	Esaki, et al.			
		4,853,076	8-1-89	Tsaur, et al.			
		4,855,245	8-8-89	Neppl, et al.			
		4,952,524	8-28-90	Lee, et al.			

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*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
		US 2001/0009784 A1	7-26-01	Ma, et al.			
		US 2002/0063292 A1	5-30-02	Armstrong, et al.			
		US 2002/0074598 A1	6-20-02	Doyle, et al.			
		US 2002/0086472	7-4-02	Roberds, et al.			

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	REF	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
							YES	NO
		JP64-76755	03-1989	Japan				

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	Kern Rim, et al., "Transconductance Enhancement in Deep Submicron Strained-Si n-MOSFETs". International Electron Devices Meeting, 26, 8, 1, IEEE, September 1998.
	Kern Rim, et al., "Characteristics and Device Design of Sub-100 nm Strained Si N- and PMOSFETs." 2002 Symposium on VLSI Technology Digest of Technical Papers, IEEE, pp. 98-99.

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INFORMATION DISCLOSURE CITATION
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		4,958,213	9-18-90	Eklund, et al.			
		5,006,913	4-9-91	Sugahara, et al.			
		5,060,030	10-22-91	Hoke, et al.			
		5,081,513	1-14-92	Jackson, et al.			
		5,108,843	4-28-92	Ohtaka, et al.			

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*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
		US 2002/0086497 A1	7-4-02	Kwok			
		US 2002/0090791 A1	7-11-02	Doyle, et al.			
		US 2003/0032261 A1	2-13-03	Yeh, et al.			
		US 2003/0040158 A1	2-27-03	Saitoh			

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F. Ootsuka, et al., "A Highly Dense, High-Performance 130nm Node CMOS Technology for Large Scale System-on-a-Chip Application." International Electron Devices Meeting, 23.5.1, IEEE, April 2000.

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*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
		5,134,085	7-28-92	Gilgen, et al.			
		5,310,446	5-10-94	Konishi, et al.			
		5,354,695	10-11-94	Leedy			
		5,371,399	12-6-94	Burroughes, et al.			
		5,391,510	2-21-95	Hsu, et al.			

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*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
		US 2003/0057184 A1	3-27-03	Yu, et al.			
		US 2003/0067035 A1	4-10-03	Tews, et al.			
		US 2004/0113174 A1	6-17-2004	Chidambarao et al.			
		US 2004/0113217 A1	6-17-2004	Chidambarao et al.			

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Shinya Ito, et al., "Mechanical Stress Effect of Etch-Stop Nitride and its Impact on Deep Submicron Transistor Design." International Electron Devices Meeting, 10.7.1, IEEE, April 2000.

A. Shimizu, et al., "Local Mechanical-Stress Control (LMC): A New Technique for CMOS-Performance Enhancement." International Electron Devices Meeting, IEEE, March 2001.

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		5,459,346	10-17-95	Asakawa, et al.			
		5,471,948	12-5-95	Burroughes, et al.			
		5,557,122	9-17-96	Shrivastava, et al.			
		5,561,302	10-1-96	Candelaria			
		5,565,697	10-15-96	Asakawa, et al.			

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		US 2004/0238914 A1	12-2-2004	Deshpande et al.			
		US 2004/0262784 A1	12-30-2004	Doris et al.			
		US 2005/0040460 A1	2-24-2005	Chidambarrao et al.			
		US 2005/0082634 A1	4-21-2005	Doris et al.			

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K. Ota, et al., "Novel Locally Strained Channel Technique for High Performance 55nm CMOS." International Electron Devices Meeting, 2.2.1, IEEE, February 2002.

G. Zhang, et al., "A New 'Mixed-Mode' Reliability Degradation Mechanism in Advanced Si and SiGe Bipolar Transistors." IEEE Transactions on Electron Devices, vol. 49, no. 12, December 2002, pp. 2151-56.

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		5,571,741	11-5-96	Leedy			
		5,592,007	1-7-97	Leedy			
		5,592,018	1-7-97	Leedy			
		5,670,798	9-23-97	Schetzina			
		5,679,965	10-21-97	Schetzina			

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*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
		US 2005/0093030 A1	5-5-2005	Doris et al.			
		US 2005/0098829 A1	5-12-2005	Doris et al.			
		US 2005/0106799 A1	5-19-2005	Doris et al.			
		US 2005/0145954 A1	7-7-2005	Zhu et al.			

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OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

H.S. Momose, et al., "Temperature Dependence of Emitter-Base Reverse Stress Degradation and its Mechanism Analyzed by MOS Structures." Paper 6.2, pp. 140-143.

C.J. Huang, et al., "Temperature Dependence and Post-Stress Recovery of Hot Electron Degradation Effects in Bipolar Transistors." IEEE 1991 Bipolar Circuits and Technology Meeting 7.5, pp. 170-173.

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		5,683,934	11-4-97	Candelaria			
		5,840,593	11-24-98	Leedy			
		5,861,651	1-19-99	Brasen, et al.			
		5,880,040	3-9-99	Sun, et al.			
		5,940,716	8-17-99	Jin, et al.			

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*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
		US 2005/0148146 A1	7-7-2005	Doris et al.			
		US 2005/0194699 A1	9-8-2005	Belvansky et al.			
		US 2005/0236668 A1	10-27-2005	Zhu et al.			
		US 2005/0245017 A1	11-3-2005	Belyansky et al.			

FOREIGN PATENT DOCUMENTS

	REF	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
							YES	NO

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S.R. Sheng, et al., "Degradation and Recovery of SiGe HBTs Following Radiation and Hot-Carrier Stressing." Pp. 14-15.

Z. Yang, et al., "Avalanche Current Induced Hot Carrier Degradation in 200 GHz SiGe Heterojunction Bipolar Transistors." Pp. 1-5.

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*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
		5,940,736	8-17-99	Brady, et al.			
		5,946,559	8-31-99	Leedy			
		5,960,297	9-28-99	Saki			
		5,989,978	11-23-99	Peldous			
		6,008,126	12-28-99	Leedy			

U.S. PATENT APPLICATION PUBLICATIONS

*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
		US 2006/0060925 A1	3-23-2006	Doris et al.			
		US 2005/0280051 A1	12-22-2005	Chidambarao et al.			
		US 2005/0282325 A1	12-22-2005	Belyansky et al.			
		US 2006/0027868 A1	2-9-2006	Doris et al.			

FOREIGN PATENT DOCUMENTS

	REF	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
							YES	NO

OTHER DOCUMENTS

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H. Li, et al., "Design of W-Band VCOs with High Output Power for Potential Application in 77 GHz Automotive Radar Systems." 2003 IEEE GaAs Digest, pp. 263-66.

H. Warzer, et al., "Annealing of Degraded npn-Transistors- Mechanisms and Modeling." IEEE Transactions on Electron Devices, vol. 41, no. 4, April 1994, pp. 533-38.

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2811

U.S. PATENT DOCUMENTS

*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
		6,025,280	2-15-00	Brady, et al.			
		6,046,464	4-4-00	Schetzina			
		6,066,545	5-23-00	Doshi, et al.			
		6,090,684	7-18-00	Ishitsuka, et al.			
		6,107,143	8-22-00	Park, et al.			

U.S. PATENT APPLICATION PUBLICATIONS

*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
		US 2006/0057787 A1	3-16-2006	Doris et al.			

FOREIGN PATENT DOCUMENTS

	REF	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
							YES	NO

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

		B. Doyle, et al., "Recovery of Hot-Carrier Damage in Reoxidized Nitrided Oxide MOSFETs." IEEE Electron Device Letters, vol. 13, no. 1, January 1992, pp. 38-40.
		H.S. Momose, et al., "Analysis of the Temperature Dependence of Hot-Carrier-Induced Degradation in Bipolar Transistors for Bi-CMOS." IEEE Transactions on Electron Devices, vol. 41, no. 6, June 1994, pp. 978-987.

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		6,117,722	9-12-00	Wuu, et al.			
		6,133,071	10-17-00	Nagai			
		6,165,383	12-26-00	Chou			
		6,221,735	4-24-01	Manley, et al.			
		6,228,694	5-8-01	Doyle, et al.			

U.S. PATENT APPLICATION PUBLICATIONS

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M. Khater, et al., "SiGe HBT Technology with $F_{max}/P_t = 350/300$ GHz and Gate Delay Below 3.3 ps". 2004 IEEE, 4 pages.

J.C. Bean, et al., "GEx Si 1-x/Si Strained-Layer Superlattice Grown by Molecular Beam Epitaxy". J. Vac. Sci. Technol. A 2(2), Apr.-June 1984, pp. 436-440.

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		6,246,095	6-12-01	Brady, et al.			
		6,255,169	7-3-01	Li, et al.			
		6,261,964	7-17-01	Wu, et al.			
		6,265,317	7-24-01	Chiu, et al.			
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U.S. PATENT APPLICATION PUBLICATIONS

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		J.H. Van Der Merve, "Regular Articles". Journal of Applied Physics, Volume 34, No. 1, January 1963, pp. 117-122.
		J.W. Matthews, et al., "Defects in Epitaxial Multilayers". Journal of Crystal Growth 27 (1974), pp. 118-125.

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		6,281,532	8-28-01	Doyle, et al.			
		6,284,623	9-4-01	Zhang, et al.			
		6,284,626	9-4-01	Kim			
		6,319,794	11-20-01	Akatsu, et al.			
		6,361,885	3-26-02	Chou			

U.S. PATENT APPLICATION PUBLICATIONS

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Subramanian S. Iyer, et al., "Heterojunction Bipolar Transistors Using Si-Ge Alloys".
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R.H.M. Van De Leur, et al., "Critical Thickness for Pseudomorphic Growth of Si/Ge Alloys
and Superlattices". J. Appl. Phys. 64 (6), 15 September 1988, pp. 3043-3050.

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		6,362,082	3-26-02	Doyle, et al.			
		6,368,931	4-9-02	Kuhn, et al.			
		6,403,486	6-11-02	Lou			
		6,403,975	6-11-02	Brunner, et al.			
		6,406,973	6-18-02	Lee			

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							YES	NO

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D.C. Houghton, et al., "Equilibrium Critical Thickness for Si 1-x Ge_x Strained Layers on (100) Si". Appl. Phys. Lett. 56 (5), 29 January 1990, pp. 460-462.

Q. Ouyang et al., "Two-Dimensional Bandgap Engineering in a Novel Si/SiGe pMOSFET with Enhanced Device Performance and Scalability". 2000 IEEE, pp. 151-154.

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		6,461,936	10-8-02	von Ehrenwall			
		6,476,462	11-5-02	Shimizu, et al.			
		6,483,171	11-19-02	Forbes, et al.			
		6,493,497	12-10-02	Ramdani, et al.			
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Huiliang Zhu

Filing Date
06/29/2004

Group Art Unit
2811

U.S. PATENT DOCUMENTS

*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
		6,501,121	12-31-02	Yu, et al.			
		6,506,652	1-14-03	Jan, et al.			
		6,509,618	1-21-03	Jan, et al.			
		6,521,964	2-18-03	Jan, et al.			
		6,531,369	3-11-03	Ozkan, et al.			

U.S. PATENT APPLICATION PUBLICATIONS

*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE

FOREIGN PATENT DOCUMENTS

	REF	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
							YES	NO

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

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INFORMATION DISCLOSURE CITATION
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Docket Number (Optional)
FIS920040116US1

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*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
		6,531,740	3-11-03	Bosco, et al.			
		6,621,392	9-16-03	Volant, et al.			
		6,635,506	10-21-03	Volant, et al.			
		6,831,292	12-14-04	Currie, et al.			
		6,717,216	4-6-04	Doris, et al.			

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*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
		6,825,529	11-30-2004	Chidambarao et al.			
		7,015,082	3-21-2006	Doris et al.			
		6,974,981	12-13-2005	Chidambarao et al.			
		6,977,194	12-20-2005	Belyansky et al.			

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